



# 100V N-Channel SGT Power MOSFET

## General Description

The SJJG016N10A uses SGT technology to provide excellent  $R_{ds(on)}$ , low gate charge and fast switching characteristics. This device is suitable for use as a wide variety of applications.

## Features

- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handling capability
- Lead free product is acquired

## Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

## Key Performance Parametes

Parameter	Value	Unit
$V_{DS}$	100	V
$R_{DS(ON\_TYP)}$	1.6	m $\Omega$
$I_D$	302	A
$Q_G$	135	nC



## Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJJG016N10A	SJJG016N10A	TO-263-7L	Tape	\	\	800 Pcs

**Table 1. Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage ( $V_{GS}=0V$ )	100	V
$V_{GS}$	Gate-Source Voltage ( $V_{DS}=0V$ )	$\pm 20$	V
$I_D$	Drain Current-Continuous( $T_C=25^\circ\text{C}$ )	302	A
	Drain Current-Continuous( $T_C=100^\circ\text{C}$ )	191	A
$I_{DM (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	1208	A
$P_D$	Maximum Power Dissipation( $T_C=25^\circ\text{C}$ )	313	W
	Maximum Power Dissipation( $T_C=100^\circ\text{C}$ )	125	W
$E_{AS}$	Avalanche energy (Note 2)	1849	mJ
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ\text{C}$

**Table 2. Thermal Characteristic**

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.4	$^\circ\text{C/W}$



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**Table 3. Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>On/Off States</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V, T_J=25^\circ\text{C}$			1	$\mu A$
		$V_{DS}=100V, V_{GS}=0V, T_J=125^\circ\text{C}$			100	$\mu A$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
$g_{FS}$	Forward Transconductance	$V_{DS}=10V, I_D=20A$		35		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=10V, I_D=20A, T_J=25^\circ\text{C}$		1.6	2.1	m $\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=50V, V_{GS}=0V, f=1.0\text{MHz}$		9820		pF
$C_{oss}$	Output Capacitance			3920		pF
$C_{rss}$	Reverse Transfer Capacitance			109		pF
$R_g$	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1.0\text{MHz}$		3.2		$\Omega$
<b>Switching Parameters</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{GS}=10V, V_{DS}=50V, R_L=2.5\Omega, R_{GEN}=6\Omega$		35		nS
$t_r$	Turn-on Rise Time			62		nS
$t_{d(off)}$	Turn-Off Delay Time			142		nS
$t_f$	Turn-Off Fall Time			110		nS
$Q_g$	Total Gate Charge	$V_{GS}=10V, V_{DS}=50V, I_D=20A$		135		nC
$Q_{gs}$	Gate-Source Charge			43		nC
$Q_{gd}$	Gate-Drain Charge			31		nC
<b>Source-Drain Diode Characteristics</b>						
$I_{SD}$	Source-Drain Current (Body Diode)				302	A
$V_{SD}$	Forward on Voltage (Note 3)	$V_{GS}=0V, I_S=20A$			1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=20A, dI/dt=500A/\mu s$		70		ns
$Q_{rr}$	Reverse Recovery Charge	$I_F=20A, dI/dt=500A/\mu s$		120		nC

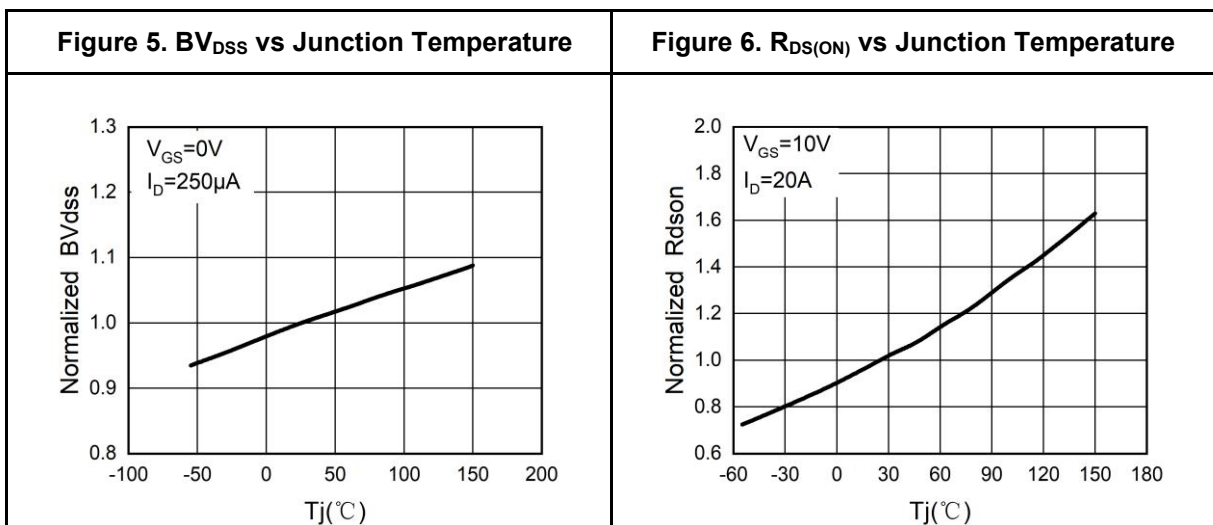
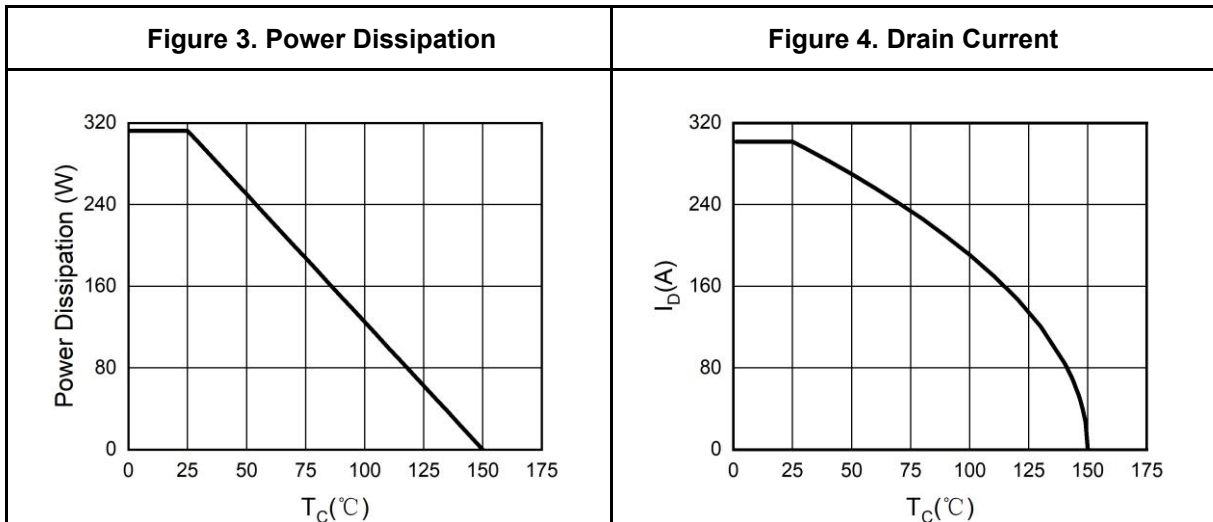
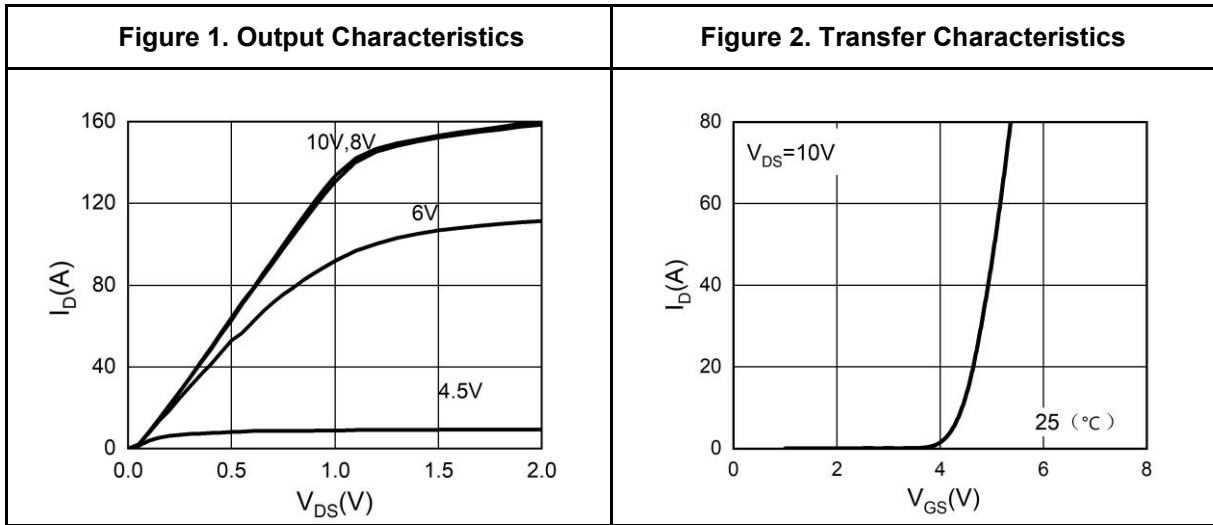
Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.EAS condition:  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, R_g=25\Omega, L=0.5\text{mH}$ .

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

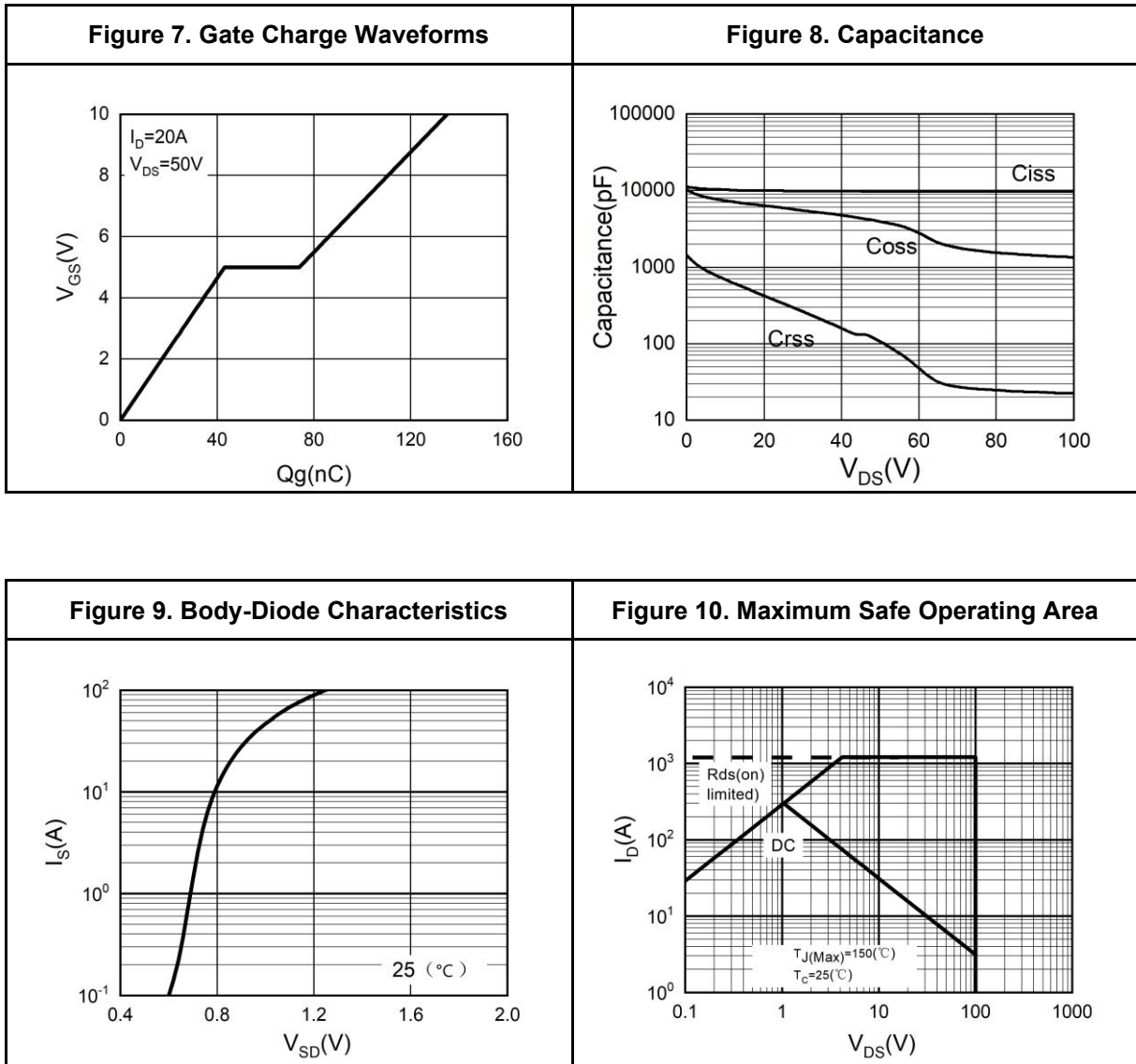


Typical Electrical And Thermal Characteristics (Curves)



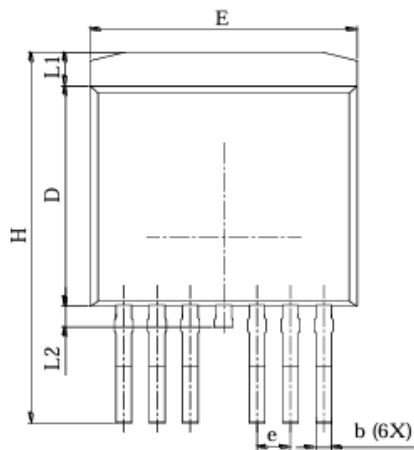


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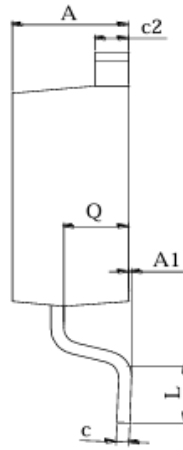




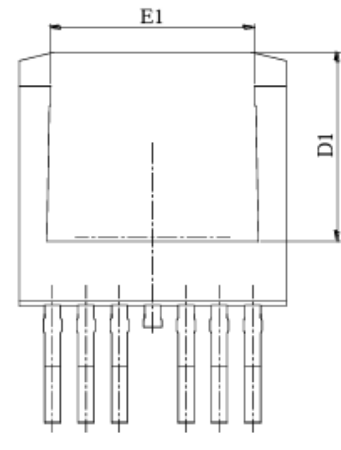
TO-263-7L Package Information



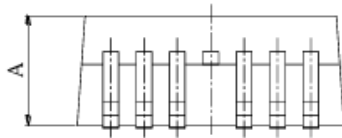
Top View



Side View



Bottom View



Front View

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	7.65 REF.		
E	9.96	10.16	10.36
E1	6.80	7.80	8.00
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.80
L1	1.36 REF.		
L2	1.20 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70



## **Attention**

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